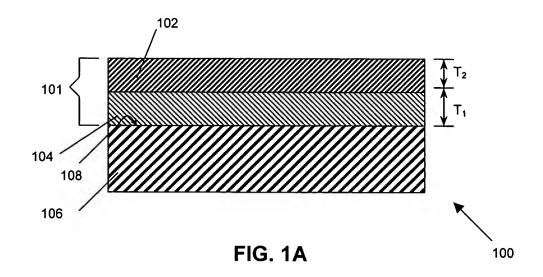
Title: METHODS FOR PRESERVING STRAINED SEMICONDUCTOR SUBSTRATE LAYERS DURING CMOS PROCESSING Inventors: Currie et al. Express Mail Label No. EV192307132US Atty Docket No.: ASC-063 Attorney for Applicants: Mark L. Beloborodov Sheet 1 of 4



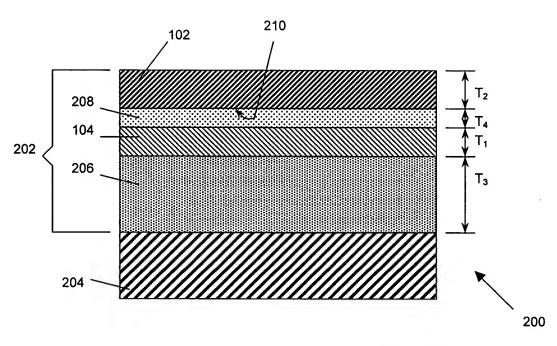
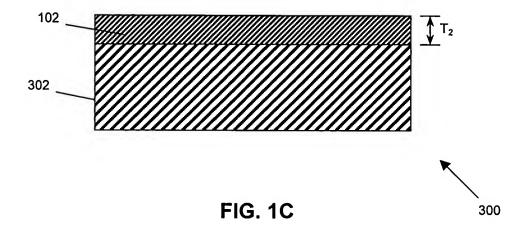


FIG. 1B

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Sheet 2 of 4



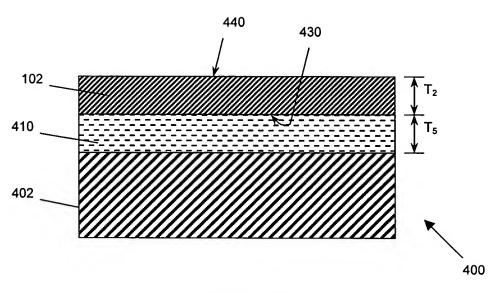
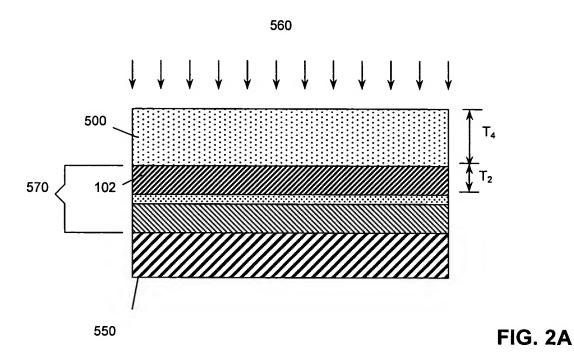
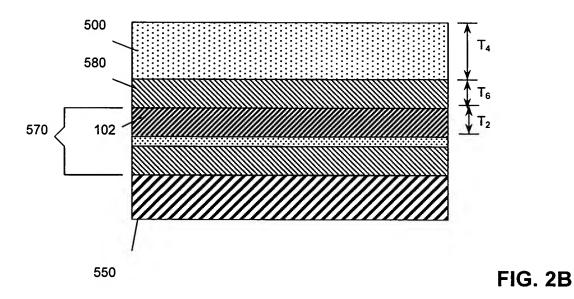


FIG. 1D

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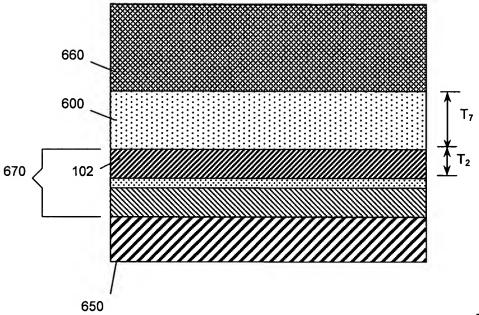


FIG. 3A

